



4N65

Power MOSFET

4A, 650V N-CHANNEL POWER MOSFET

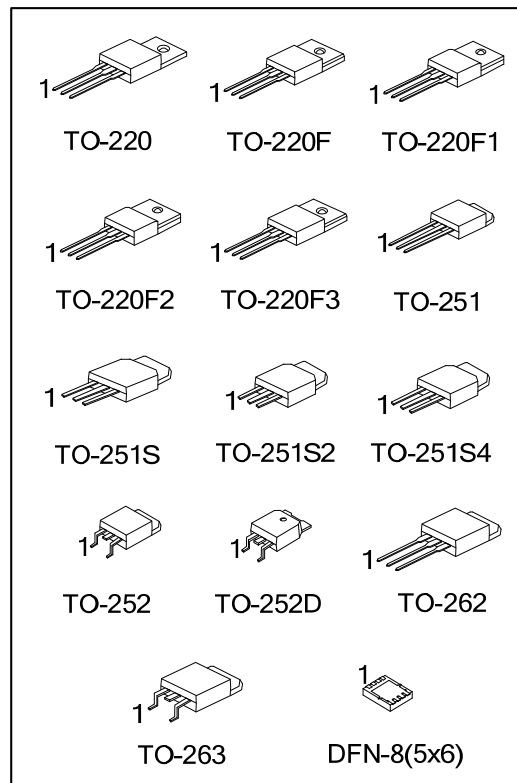
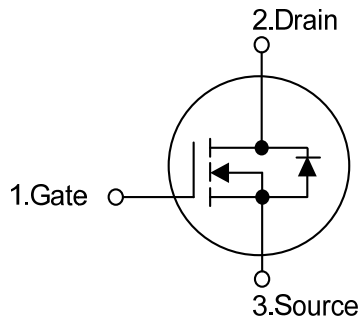
DESCRIPTION

The UTC **4N65** is a high voltage power MOSFET designed to have better characteristics, such as fast switching time, low gate charge, low on-state resistance and have a high rugged avalanche characteristic. This power MOSFET is usually used in high speed switching applications including power supplies, PWM motor controls, high efficient DC to DC converters and bridge circuits.

FEATURES

- * $R_{DS(ON)} < 2.5\Omega$ @ $V_{GS} = 10V, I_D = 2.2A$
- * Fast Switching Capability
- * Avalanche Energy Specified
- * Improved dv/dt Capability, High Ruggedness

SYMBOL



ORDERING INFORMATION

Ordering Number		Package	Pin Assignment								Packing
Lead Free	Halogen Free		1	2	3	4	5	6	7	8	
4N65L-TA3-T	4N65G-TA3-T	TO-220	G	D	S	-	-	-	-	-	Tube
4N65L-TF1-T	4N65G-TF1-T	TO-220F1	G	D	S	-	-	-	-	-	Tube
4N65L-TF2-T	4N65G-TF2-T	TO-220F2	G	D	S	-	-	-	-	-	Tube
4N65L-TF3-T	4N65G-TF3-T	TO-220F	G	D	S	-	-	-	-	-	Tube
4N65L-TF3T-T	4N65G-TF3T-T	TO-220F3	G	D	S	-	-	-	-	-	Tube
4N65L-TM3-T	4N65G-TM3-T	TO-251	G	D	S	-	-	-	-	-	Tube
4N65L-TMS-T	4N65G-TMS-T	TO-251S	G	D	S	-	-	-	-	-	Tube
4N65L-TMS2-T	4N65G-TMS2-T	TO-251S2	G	D	S	-	-	-	-	-	Tube
4N65L-TMS4-T	4N65G-TMS4-T	TO-251S4	G	D	S	-	-	-	-	-	Tube
4N65L-TN3-R	4N65G-TN3-R	TO-252	G	D	S	-	-	-	-	-	Tape Reel
4N65L-TND-R	4N65G-TND-R	TO-252D	G	D	S	-	-	-	-	-	Tape Reel
4N65L-T2Q-T	4N65G-T2Q-T	TO-262	G	D	S	-	-	-	-	-	Tube
4N65L-TQ2-R	4N65G-TQ2-R	TO-263	G	D	S	-	-	-	-	-	Tape Reel
4N65L-TQ2-T	4N65G-TQ2-T	TO-263	G	D	S	-	-	-	-	-	Tube
4N65G-K08-5060-R	4N65G-K08-5060-R	DFN-8(5×6)	S	S	S	G	D	D	D	D	Tape Reel

Note: Pin Assignment: G: Gate D: Drain S: Source

4N65G-TA3-T

(1) Packing Type
(2) Package Type
(3) Green Package

(1) T: Tube, R: Tape Reel
 (2) TA3: TO-220, TF1: TO-220F1, TF2: TO-220F2
 TF3: TO-220F, TF3T: TO-220F3, TM3: TO-251,
 TMS: TO-251S, TMS2: TO-251S2, TN3: TO-252,
 TMS4: TO-251S4, TND: TO-252D, T2Q: TO-262,
 TQ2: TO-263, K08-5060: DFN-8(5×6)
 (3) G: Halogen Free and Lead Free, L: Lead Free

MARKING

PACKAGE	MARKING
TO-220 TO-220F TO-220F1 TO-220F2 TO-220F3 TO-251 TO-251S TO-251S2 TO-251S4 TO-252 TO-252D TO-262 TO-263	<p>UTC 4N65 Lot Code ← [] [] [] [] [] → Data Code</p>
DFN-8(5×6)	<p>UTC 4N65 Lot Code ← [] [] [] [] [] → Date Code</p>

■ ABSOLUTE MAXIMUM RATINGS ($T_C = 25^\circ\text{C}$, unless otherwise specified)

PARAMETER		SYMBOL	RATINGS	UNIT
Drain-Source Voltage		V_{DSS}	650	V
Gate-Source Voltage		V_{GSS}	± 30	V
Avalanche Current (Note2)		I_{AR}	4.4	A
Drain Current	Continuous	I_D	4.0	A
	Pulsed (Note2)	I_{DM}	16	A
Avalanche Energy	Single Pulsed (Note3)	E_{AS}	260	mJ
	Repetitive (Note2)	E_{AR}	10.6	mJ
Peak Diode Recovery dv/dt (Note4)		dv/dt	4.5	V/ns
Power Dissipation	TO-220/TO-262/TO-263	P_D	106	W
	TO-220F/TO-220F1 TO-220F3		35	W
	TO-220F2		36	W
	TO-251/ TO-251S TO-251S2/TO-251S4 TO-252/TO-252D		50	W
	DFN-8(5×6)		30	W
Junction Temperature		T_J	+150	$^\circ\text{C}$
Operating Temperature		T_{OPR}	-55 ~ +150	$^\circ\text{C}$
Storage Temperature		T_{STG}	-55 ~ +150	$^\circ\text{C}$

Note: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged.

Absolute maximum ratings are stress ratings only and functional device operation is not implied.

2. Repetitive Rating: Pulse width limited by maximum junction temperature.

3. $L = 30\text{mH}$, $I_{AS} = 4\text{A}$, $V_{DD} = 50\text{V}$, $R_G = 25\ \Omega$, Starting $T_J = 25^\circ\text{C}$

4. $I_{SD} \leq 4.4\text{A}$, $di/dt \leq 200\text{A}/\mu\text{s}$, $V_{DD} \leq BV_{DSS}$, Starting $T_J = 25^\circ\text{C}$

■ THERMAL DATA

PARAMETER	PACKAGE	SYMBOL	RATINGS	UNIT
Junction to Ambient	TO-220/TO-262/TO-263 TO-220F/TO-220F1 TO-220F2/TO-220F3	θ_{JA}	62.5	$^\circ\text{C}/\text{W}$
	TO-251/ TO-251S TO-251S2/TO-251S4 TO-252/TO-252D		110	$^\circ\text{C}/\text{W}$
	DFN-8(5×6)		75	$^\circ\text{C}/\text{W}$
Junction to Case	TO-220/TO-262/TO-263	θ_{JC}	1.18	$^\circ\text{C}/\text{W}$
	TO-220F/TO-220F1 TO-220F3		3.5	$^\circ\text{C}/\text{W}$
	TO-220F2		3.4	$^\circ\text{C}/\text{W}$
	TO-251/ TO-251S TO-251S2/TO-251S4 TO-252/TO-252D		2.5	$^\circ\text{C}/\text{W}$
	DFN-8(5×6)		4.17	$^\circ\text{C}/\text{W}$

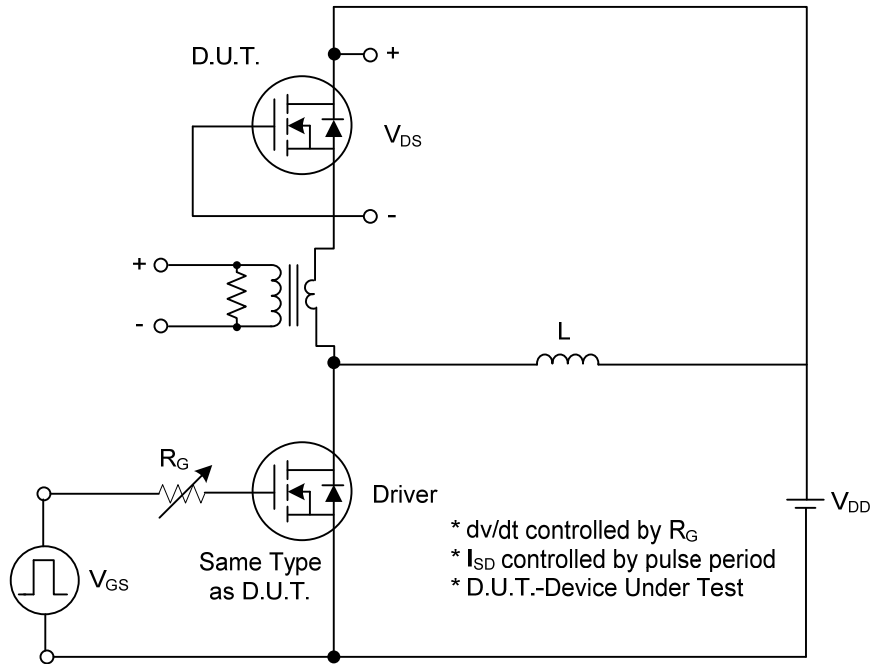
■ ELECTRICAL CHARACTERISTICS ($T_C=25^\circ\text{C}$, unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT	
OFF CHARACTERISTICS							
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS} = 0\text{ V}, I_D = 250\mu\text{A}$	650			V	
Drain-Source Leakage Current	I_{DSS}	$V_{DS} = 650\text{ V}, V_{GS} = 0\text{ V}$			10	μA	
		$V_{DS} = 480\text{ V}, T_C = 125^\circ\text{C}$			100	μA	
Gate-Source Leakage Current	Forward Reverse	I_{GSS}	$V_{GS} = 30\text{ V}, V_{DS} = 0\text{ V}$			100	nA
			$V_{GS} = -30\text{ V}, V_{DS} = 0\text{ V}$			-100	nA
Breakdown Voltage Temperature Coefficient	$\Delta BV_{DSS}/\Delta T_J$	$I_D = 250\mu\text{A}$, Referenced to 25°C		0.6		$\text{V}/^\circ\text{C}$	
ON CHARACTERISTICS							
Gate Threshold Voltage	$V_{GS(TH)}$	$V_{DS} = V_{GS}, I_D = 250\mu\text{A}$	2.0		4.0	V	
Static Drain-Source On-State Resistance	$R_{DS(ON)}$	$V_{GS} = 10\text{ V}, I_D = 2.2\text{A}$		2.4	2.5	Ω	
DYNAMIC CHARACTERISTICS							
Input Capacitance	C_{ISS}	$V_{DS} = 25\text{ V}, V_{GS} = 0\text{V},$ $f = 1\text{MHz}$		670	750	pF	
Output Capacitance	C_{OSS}				70	90	pF
Reverse Transfer Capacitance	C_{RSS}				23	26	pF
SWITCHING CHARACTERISTICS							
Turn-On Delay Time	$t_{D(ON)}$	$V_{DS} = 325\text{V}, I_D = 4.0\text{A},$ $R_G = 25\Omega$ (Note 1, 2)		45	85	ns	
Turn-On Rise Time	t_R				100	140	ns
Turn-Off Delay Time	$t_{D(OFF)}$				200	240	ns
Turn-Off Fall Time	t_F				130	150	ns
Total Gate Charge	Q_G	$V_{DS} = 520\text{V}, I_D = 4.0\text{A},$ $V_{GS} = 10\text{V}$ (Note 1, 2)		100	120	nC	
Gate-Source Charge	Q_{GS}				17	19	nC
Gate-Drain Charge	Q_{GD}				20	26	nC
SOURCE- DRAIN DIODE RATINGS AND CHARACTERISTICS							
Drain-Source Diode Forward Voltage	V_{SD}	$V_{GS} = 0\text{ V}, I_S = 4.4\text{A}$			1.4	V	
Maximum Continuous Drain-Source Diode Forward Current	I_S				4.4	A	
Maximum Pulsed Drain-Source Diode Forward Current	I_{SM}				17.6	A	
Reverse Recovery Time	t_{rr}	$V_{GS} = 0\text{V}, I_S = 4.4\text{A},$		250		ns	
Reverse Recovery Charge	Q_{RR}	$di/dt = 100\text{ A}/\mu\text{s}$ (Note 1)		1.5		μC	

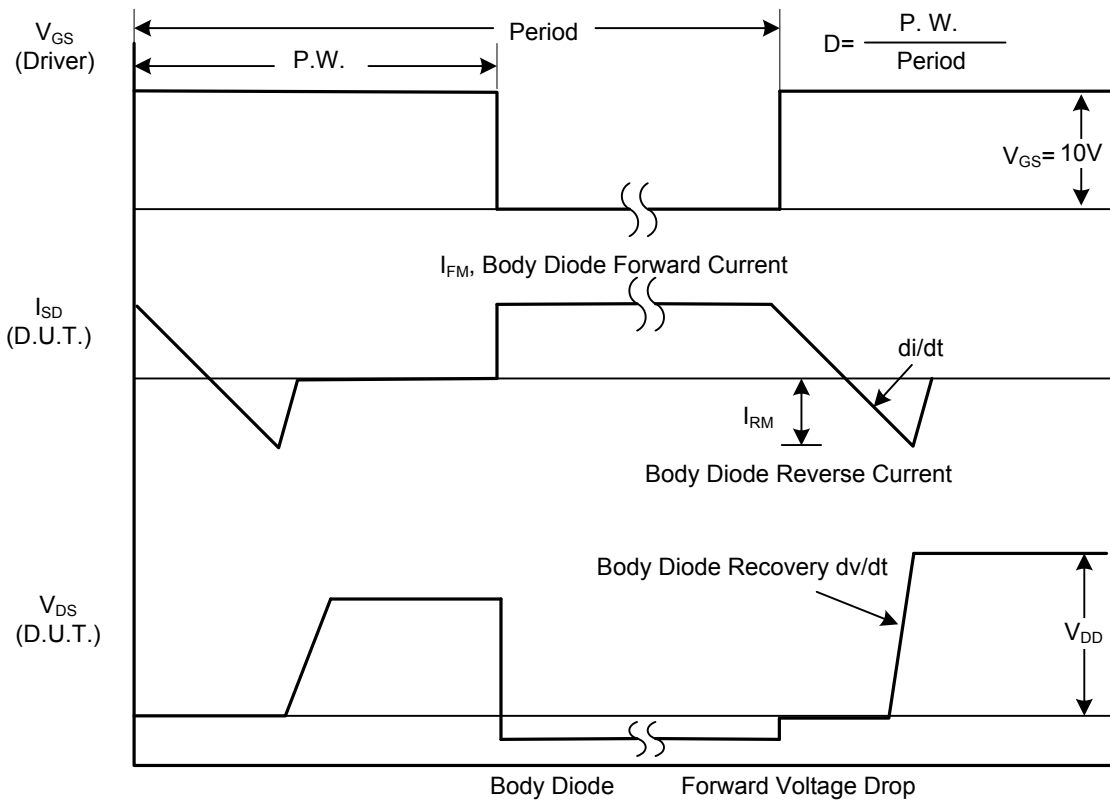
Note: 1. Pulse Test: Pulse width $\leq 300\mu\text{s}$, Duty cycle $\leq 2\%$.

2. Essentially independent of operating temperature.

■ TEST CIRCUITS AND WAVEFORMS

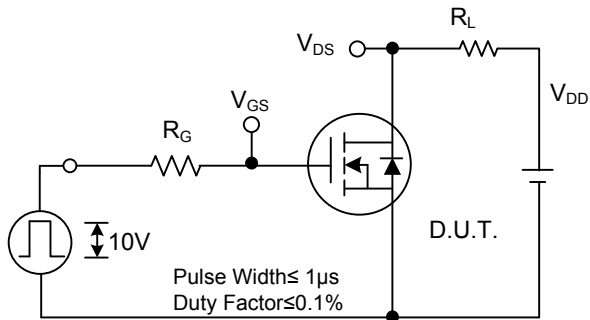


Peak Diode Recovery dv/dt Test Circuit

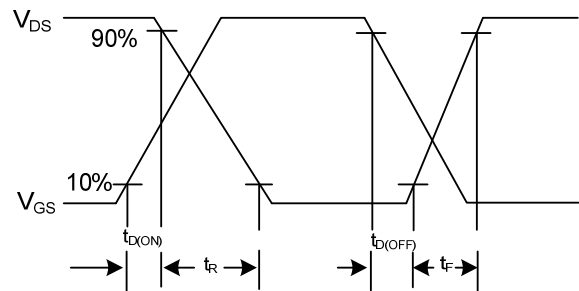


Peak Diode Recovery dv/dt Waveforms

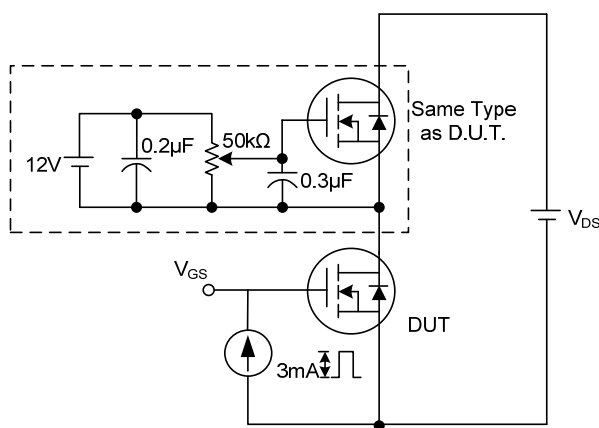
■ TEST CIRCUITS AND WAVEFORMS (Cont.)



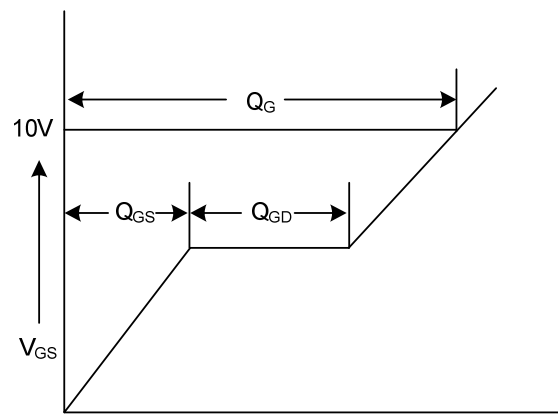
Switching Test Circuit



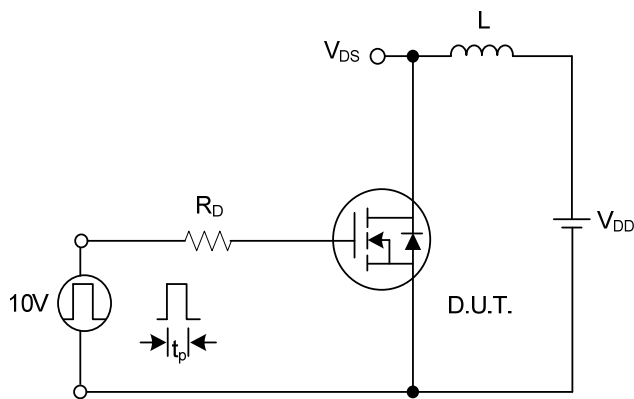
Switching Waveforms



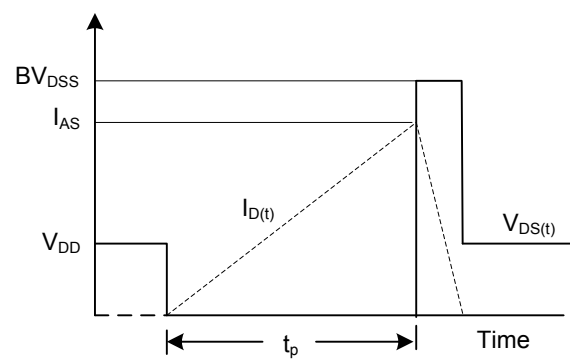
Gate Charge Test Circuit



Gate Charge Waveform

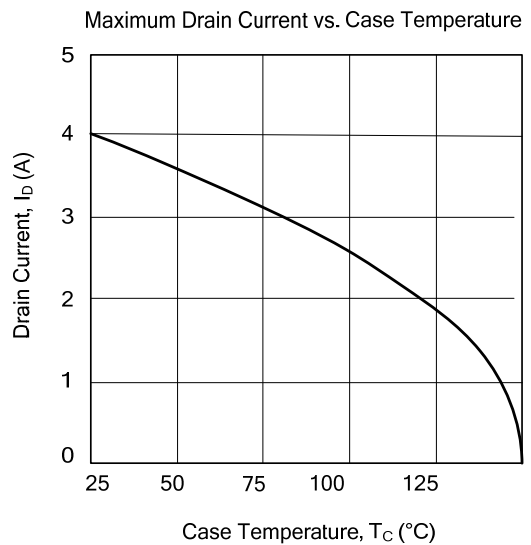
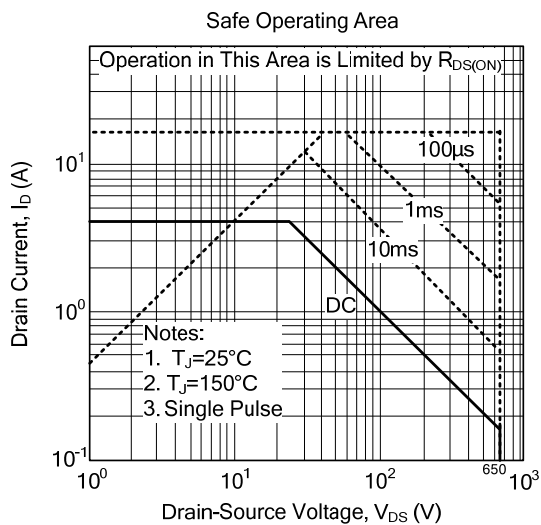
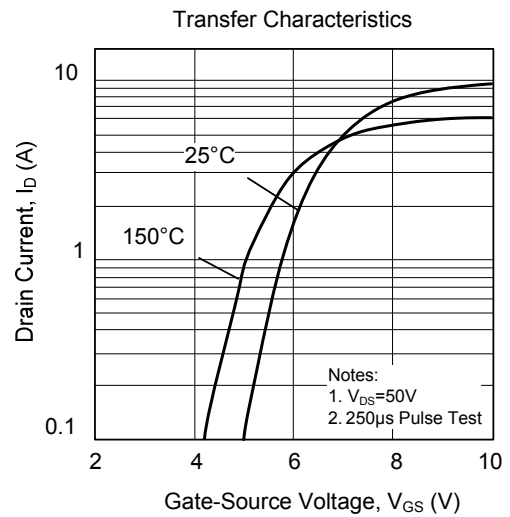
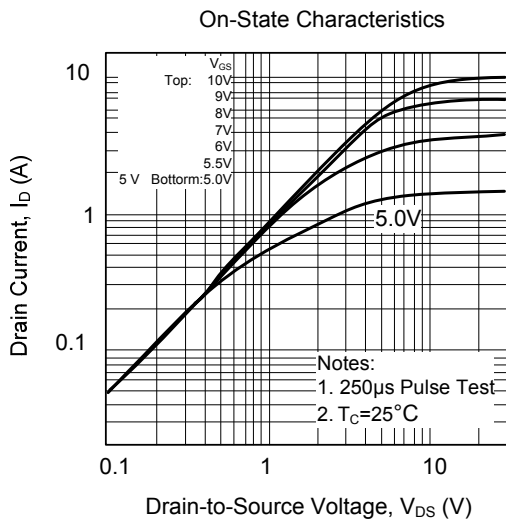
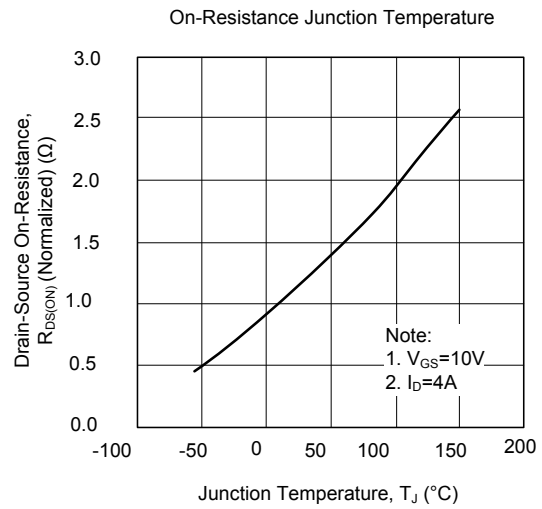
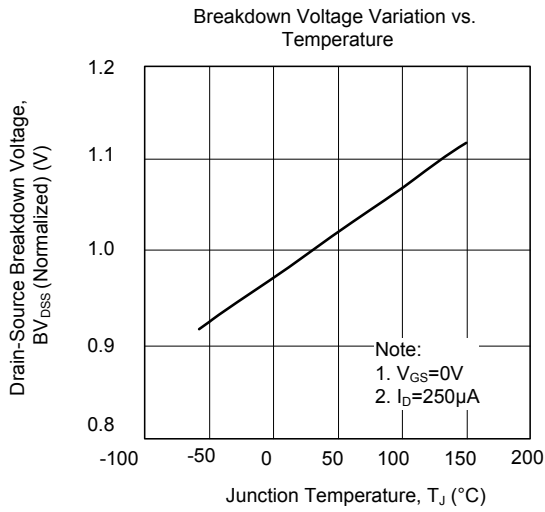


Unclamped Inductive Switching Test Circuit



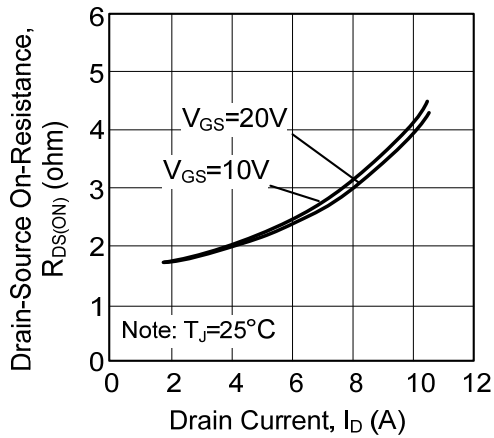
Unclamped Inductive Switching Waveforms

TYPICAL CHARACTERISTICS

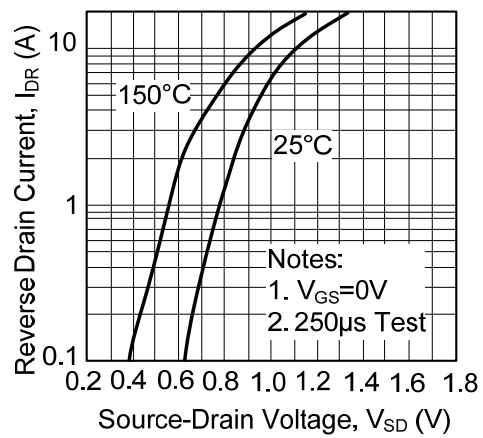


■ TYPICAL CHARACTERISTICS(Cont.)

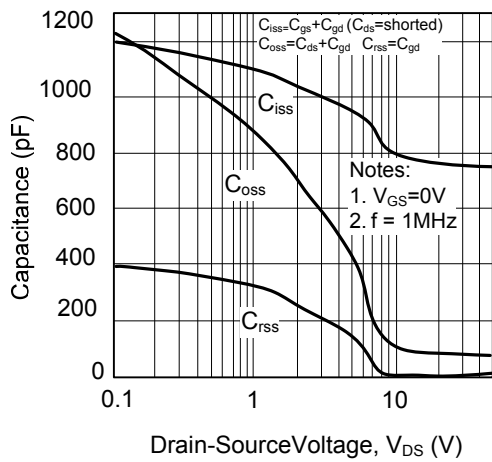
On-Resistance Variation vs. Drain Current and Gate Voltage



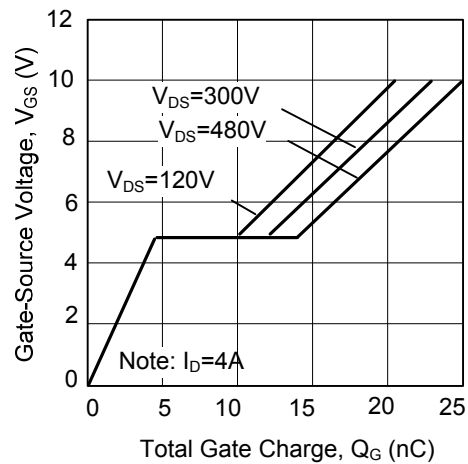
On State Current vs. Allowable Case Temperature



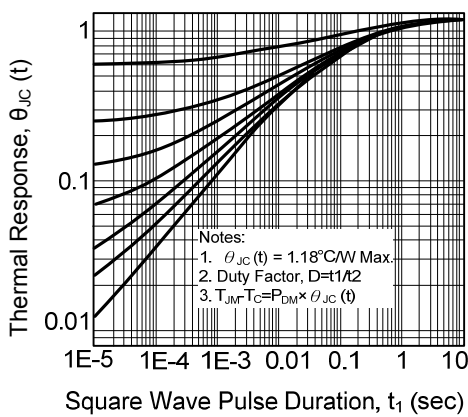
Capacitance Characteristics (Non-Repetitive)



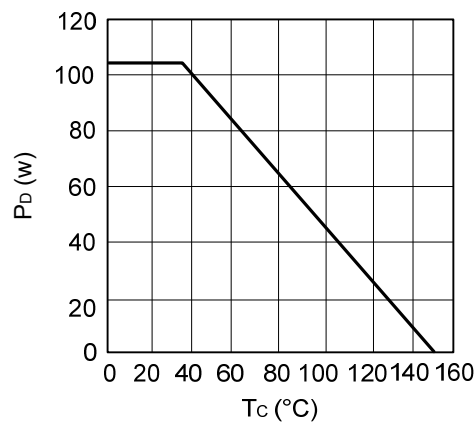
Gate Charge Characteristics



Transient Thermal Response Curve



Power Dissipation



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